

Title (en)

FLOATING GATE MEMORY CELL WITH CHARGE LEAKAGE PREVENTION

Title (de)

SPEICHERZELLE MIT SCHWEBENDEM GATE UND VERHINDERUNG DER LADUNGSVERLUSTEN

Title (fr)

CELLULE MEMOIRE A GRILLE FLOTTANTE PREVENANT LES FUITES DE CHARGES

Publication

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Application

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Priority

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Abstract (en)

[origin: WO9850960A1] A process for fabricating a floating gate memory cell (60) with reduced charge leakage. An oxide regrowth (73) is formed over the sides of the floating gate (69) and is then covered with an oxide protective coating (64, 66). The structure is applicable to salicide and non-salicide memory cells and is especially useful in floating gate memory cells with gate stacks having abnormally shaped side walls.

IPC 1-7

H01L 29/788

IPC 8 full level

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CPC (source: EP KR)

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